

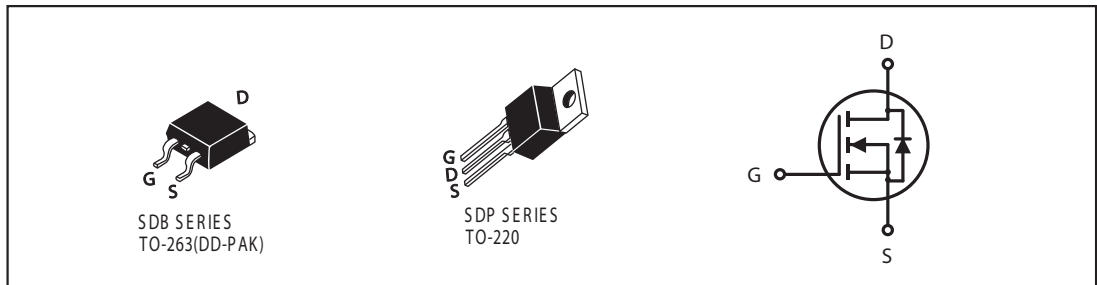


N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(on)} (mΩ) Max
30V	70A	7 @ V _{GS} = 10V
		11 @ V _{GS} = 4.5V

FEATURES

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- TO-220 & TO-263 package.

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous @ T _J =125°C -Pulsed ^a	I _D	70	A
	I _{DM}	210	A
Drain-Source Diode Forward Current	I _S	75	A
Maximum Power Dissipation @ T _C =25°C	P _D	75	W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	2	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	°C/W

SDP/B75N03L

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	35		V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			10	uA
Gate-Body Leakage	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS ^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.5	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =37A		6	7	m ohm
		V _{GS} =4.5V, I _D =30A		9	11	m ohm
On-State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =10V	60			A
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =37A		47		S
DYNAMIC CHARACTERISTICS ^b						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V f=1.0MHz		1900		pF
Output Capacitance	C _{OSS}			960		pF
Reverse Transfer Capacitance	C _{RSS}			320		pF
SWITCHING CHARACTERISTICS ^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =15V, I _D =1A, V _{GEN} =10V R _G =1.8 ohm R _L =0.20 ohm		15		ns
Rise Time	t _r			12.5		ns
Turn-Off Delay Time	t _{D(OFF)}			5.5		ns
Fall Time	t _f			6.5		ns
Total Gate Charge	Q _g	V _{DS} =24V, I _D =75A, V _{GS} =10V		61		nC
		V _{DS} =24V, I _D =75A, V _{GS} =4.5V		32		nC
Gate-Source Charge	Q _{gs}	V _{DS} =24V, I _D =75A, V _{GS} =10V		11		nC
Gate-Drain Charge	Q _{gd}			11		nC

SDP/B75N03L

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^a						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 37A$		0.93	1.3	V

Notes

- a. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

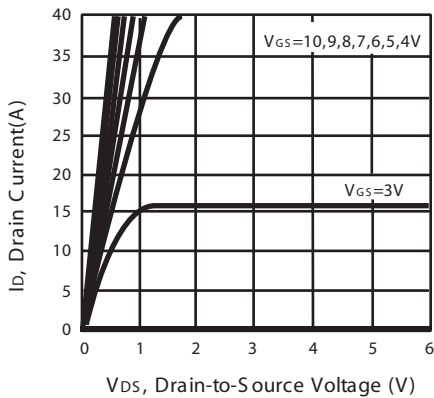


Figure 1. Output Characteristics

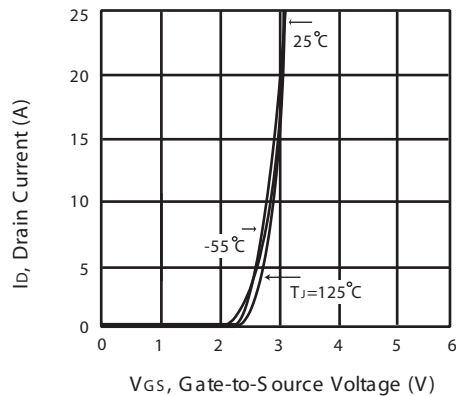


Figure 2. Transfer Characteristics

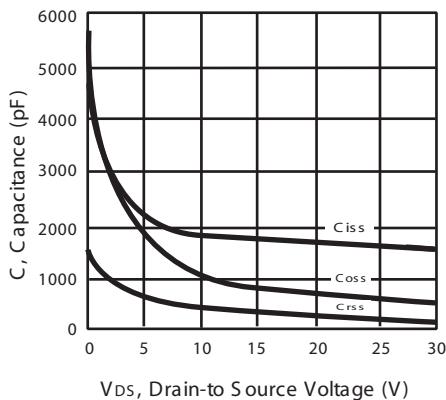


Figure 3. Capacitance

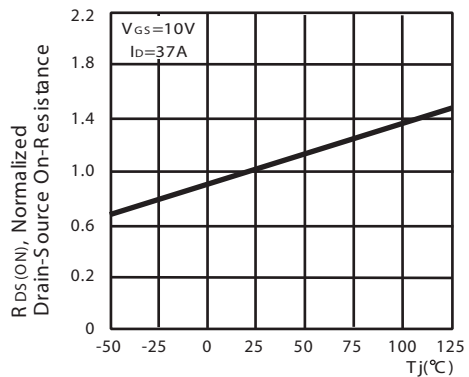


Figure 4. On-Resistance Variation with Temperature

SDP/B75N03L

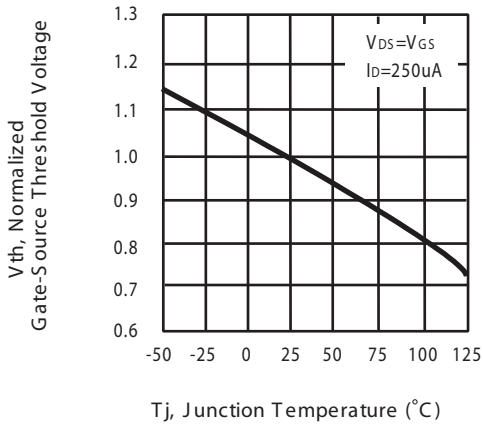


Figure 5. Gate Threshold Variation with Temperature

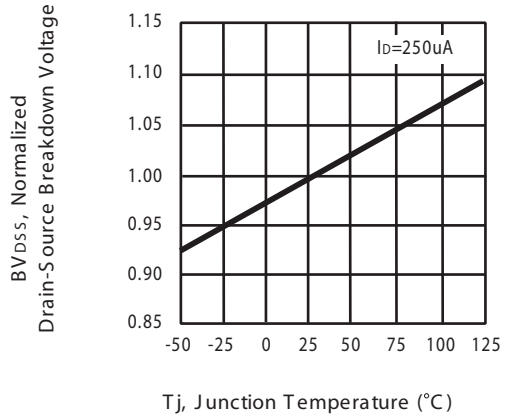


Figure 6. Breakdown Voltage Variation with Temperature

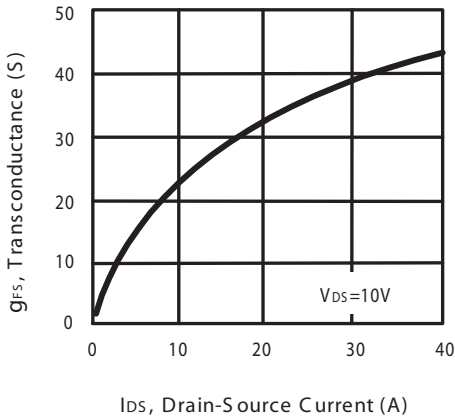


Figure 7. Transconductance Variation with Drain Current

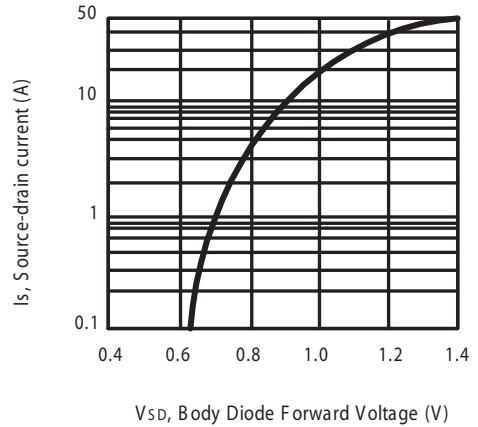


Figure 8. Body Diode Forward Voltage Variation with Source Current

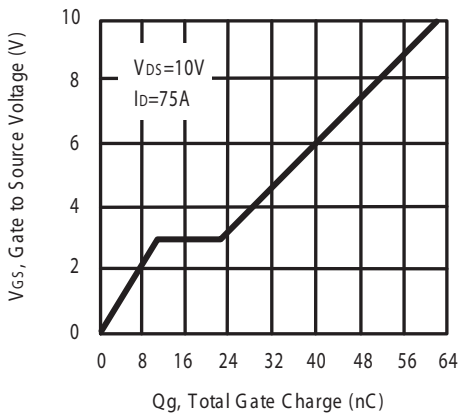


Figure 9. Gate Charge

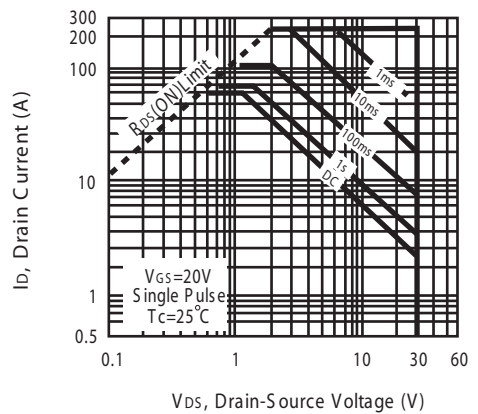


Figure 10. Maximum Safe Operating Area

SDP/B75N03L

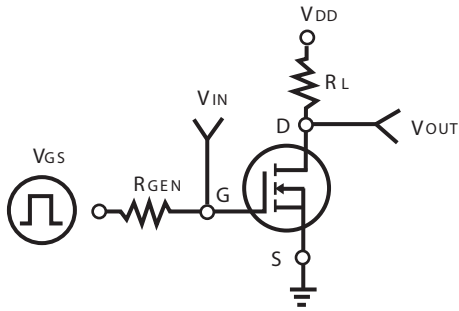


Figure 11. Switching Test Circuit

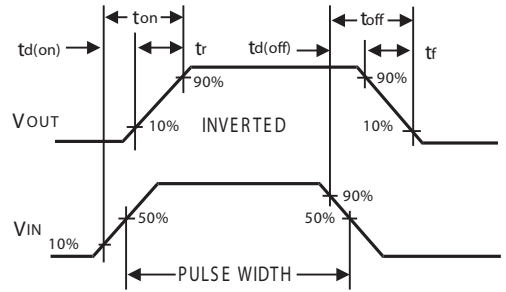


Figure 12. Switching Waveforms

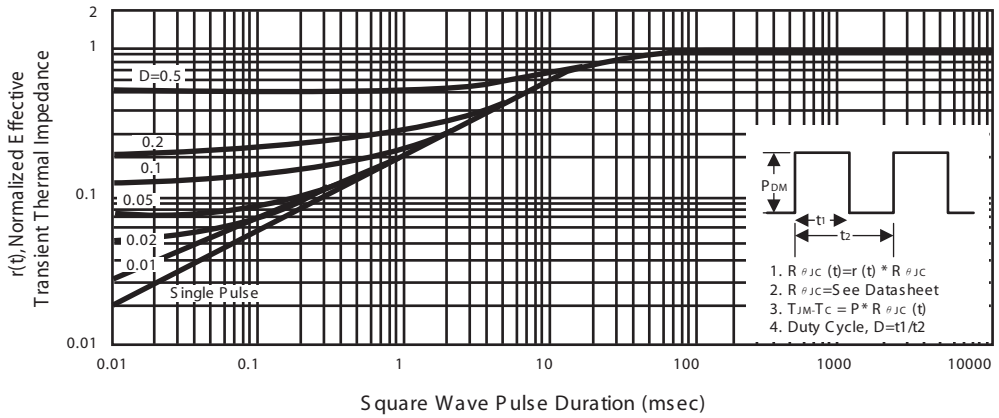
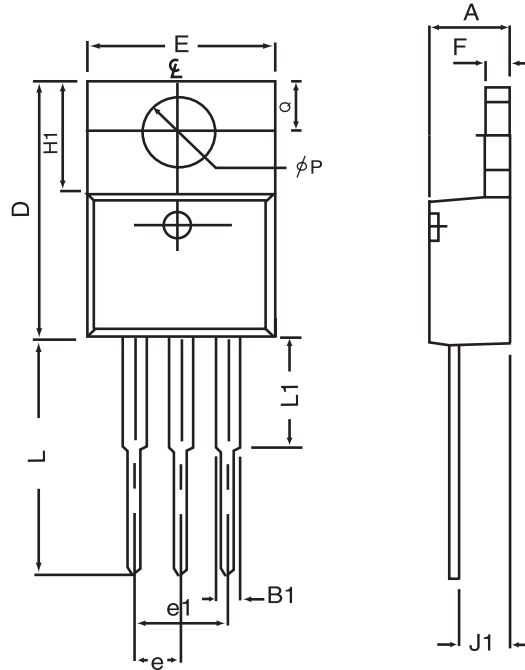


Figure 13. Normalized Thermal Transient Impedance Curve

SDP/B75N03L

PACKAGE OUTLINE DIMENSIONS

TO-220



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	4.80	0.170	0.189
B1	1.27	1.65	0.050	0.630
D	14.6	16.00	0.575	0.610
E	9.70	10.41	0.382	0.410
e	2.34	2.74	0.092	0.108
e1	4.68	5.48	0.184	0.216
F	1.14	1.40	0.045	0.055
H1	5.97	6.73	0.235	0.265
J1	2.20	2.79	0.087	0.110
L	12.88	14.22	0.507	0.560
L1	3.00	6.35	0.120	0.250
ϕP	3.50	3.94	0.138	0.155
Q	2.54	3.05	0.100	0.120